

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

1N4933G THRU 1N4937G

GLASS PASSIVATED FAST RECOVERY RECTIFIER

TECHNICAL SPECIFICATION

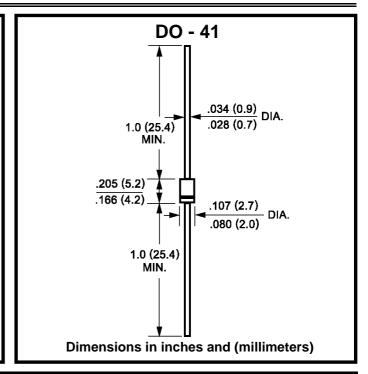
VOLTAGE: 50 TO 600V CURRENT: 1.0A

FEATURES

- Molded case feature for auto insertion
- Glass passivated chip
- Fast switching for high efficiency
- High current capability
- Low leakage current
- High surge capability
- High temperature soldering guaranteed: 250°C/10sec/0.375"(9.5mm) lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode
- Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	1N 4933G	1N 4934G	1N 4935G	1N 4936G	1N 4937G	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	V
Maximum Average Forward Rectified Current	_	1.0					А
(9.5mm lead length, at T _a =75°C)	I _{F(AV)}						
Peak Forward Surge Current (8.3ms single	leo.	30.0					А
half sine-wave superimposed on rated load)	I _{FSM}						
Maximum Forward Voltage	V_{F}	1.2					V
(at rated forward current and 25°C)	۷F						
Maximum DC Reverse Current T _a =25°C	_	5.0					μΑ
(at rated DC blocking voltage) T _a =100°C	I _R	100					μΑ
Maximum Reverse Recovery Time (Note 1)	trr	200					nS
Typical Junction Capacitance (Note 2)	C_J	15.0					рF
Typical Thermal Resistance (Note 3)	R _θ (ja)	50.0					°C/W
Storage and Operation Junction Temperature	T_{STG}, T_{J}	-65 to +150					°C

Note:

- 1.Reverse recovery condition I_F=1.0A, V_R=30V
- 2.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
- 3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C. board mounted